PS3P0143P1

General Description

This device has been developed using Trench technology, these products have been designed to minimize on-state resistance and fast switching performance. These products are suited for load switch and protection applications.

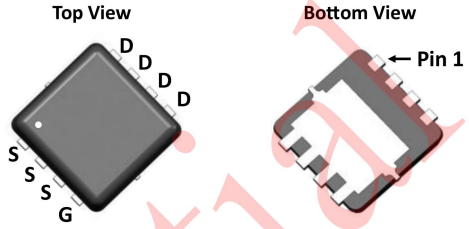
30V P-Channel MOSFETs

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max.	ID
-30 V	8.5 mΩ @ -10 V	-50 A
	14 mΩ @ -4.5 V	

Features

- Low On-Resistance
- RoHS Compliant and Halogen Free

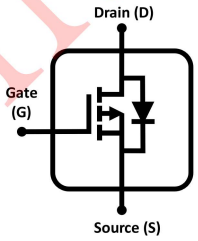
PPAK 3333



Applications

- Load Switch
- Battery Protection

Pin Configuration



Absolute Maximum Ratings (T_J=25°C, unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-Source Voltage		-30	V
V_{GS}	Gate-Source Voltage		±20	
I_D	Drain Current-Continuous [A]	T_C=25 °C	-50	A
		T_C=100 °C	-32	
I_{DM}	Drain Current-Pulsed [A, B]	T_C=25°C	-200	A
I_{AS}	Non-repetitive Avalanche Current [E]		TBD	A
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy [E]		TBD	mJ
P_D	Maximum Power Dissipation	T_C=25 °C	59	W
		T_C=100 °C	23	
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Junction-to-Ambient [C]	Steady State	62	°C/W
$R_{\theta JC}$	Junction-to-Case	Steady State	2.1	°C/W